



**SMD1-7 Case
1N914B Diodes**

ELECTRICAL CHARACTERISTICS at 25 °C

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
V_{BR}	Breakdown Voltage	100		V	$I_R=10 \text{ uA}$
V_F	Forward Voltage		1.0	V	$I_F=100 \text{ mA}$
I_R	Reverse Current		4.0 200	μA μA	$V_R=75 \text{ V}$, $T_A=25^\circ\text{C}$ $V_R=75 \text{ V}$, $T_A=125^\circ\text{C}$
C	Capacitance (Note 1)		5.0	pF	$V_R=0$, $f=1.0\text{MHz}$
t_{fr}	Forward Recovery Time		20	ns	$I_F=100 \text{ mA}$, $R_s=50 \text{ ohms}$ $V_{fr}=1.1\text{V}$, $t_i \leq 1 \text{ ns}$
t_{rr}	Reverse Recovery Time		4.0	ns	$I_F=I_R=10 \text{ mA}$, $R_L=100 \text{ ohms}$, $I_{rr}=1.0 \text{ mA}$

Notes:

1. The capacitance is measured from pin to pin across any one of the diodes. The interaction of other diodes is therefore included in the measured value.